EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2	("20060240640").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/06/03 13:34
S2	6	(("4124401") or ("5769986") or ("6261927")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/06/03 13:37
S3	6	isostatic wafer bond$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2008/06/03 14:04
S4	1192	isostatic bond$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2008/06/03 14:05
S5	1	S4 and (substrate wafer disc)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2008/06/03 14:06
S6	584	S4 and (substrate wafer disc)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:06
S7	198	S6 and clean$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:06
S8	74	S7 and (hydrogen waals)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:32

S9	74	S7 and hydrogen	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:32
S10	1	S7 and waals	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:32
S11	0	S7 and hydrogen near3 termination	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:33
S12	0	S7 and hydrogen near3 termina4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:33
S13	0	S7 and hydrogen near3 termin	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:34
S14	1	S7 and hydrogen near3 termin$5	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:34
S15	153	cleaning with hydrogen near3 termin$5 near3 surface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:34
S16	137	bond$4 same (substrate wafer disc)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2008/06/03 14:43
S17	367817	bond$4 same (substrate wafer disc)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:43

S18	122628	S17 and (heat$4 and (pressur$3 pressuriz$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:44
S19	3307	S18 and waals	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:44
S20	2002	S19 and (hydrogen with termin$5 hydrophobic hf)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:45
S21	9	S20 and isostatic	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:45
S22	266461	bond$4 with (substrate wafer disc)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:47
S23	1342	S20 and S22	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:47
S24	159690	bond$4 near3 (substrate wafer disc)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:47
S25	841	S24 and S20	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:48
S26	2	"20060240640"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/04 09:14

S27	1846	wafer near3 bond$4 with (pressure compression)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/04 09:35
S28	1391	S27 and temperature	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/04 09:36
S29	1214	S28 and silicon	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/04 09:36
S30	78	S29 and waals	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/04 09:37
S31	1	S30 and isostatic	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/04 09:41
S32	9	S27 and isostatic	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/04 09:42
S33	5	(("6723379") or ("6627814")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/06/04 09:44
S34	1888	isostatic adj press	US-PGPUB; USPAT	OR	ON	2008/06/04 09:45
S35	965	hot adj isostatic adj press	US-PGPUB; USPAT	OR	ON	2008/06/04 09:45
S36	10	wafer near3 bond$4 and S34	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/04 09:45

S37	52	wafer near3 bond$4 and isostatic	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/04 09:47
S38	55	clean$4 and S30	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/04 09:50
S39	34	unsealed and isostatic	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/04 11:42
S40	0	gass adj pressure adj bonding with wafer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/04 11:44
S41	575768	HIP same bond saem wafer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/30 14:22
S42	7	HIP same bond same wafer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/30 14:22
S43	6	HIP with bond$3 with wafer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/30 14:23
S44	120	HIP with bond$3 with substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/30 14:24
S45	111	isostatic with bond$3 with substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/30 14:28

S46	45	isostatic with wafer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/30 14:38
S47	23	isostatic adj bond$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/30 14:43
S48	2	("5207864").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/02/27 10:23
S49	2	("7,276,789").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/02/27 10:35
S50	131	hip and compression with bond$4 and (silicon semiconductor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/27 14:33
S51	18	hip same compression with bond$4 and (silicon semiconductor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/27 14:34
S52	72	weak adj bond$5 and isostatic	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/10 13:58
S53	11	S52 and wafer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/10 13:58
S54	73	isostatic with bond$5 and wafer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/10 14:00

S55	1	S54 and waals	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/10 14:01
S56	562	wafer with bonding and pressure adj chamber	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/12 15:22
S57	47	wafer with bonding and pressure adj chamber same argon	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/12 15:23
S58	5	isostatic adj pressure adj chamber same argon	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/12 15:29
S59	4	isostatic adj pressure adj chamber and semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/12 15:31
S60	5	("3523148").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/12 15:39
S61	2	("6189766").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/12 15:44
S62	2	("4478626").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/12 15:46
S63	3	("4168957").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/12 15:47

S64	2	("6464129").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/12 15:50
S65	48	(US-20020154280-$ or US-20030088980-$ or US-20030206818-$ or US-20020069906-$ or US-20090078570-$ or US-20090072428-$ or US-20070060969-$ or US-20050257877-$ or US-20050115045-$ or US-20030134143-$ or US-20060240640-$ or US-20050241147-$ or US-20060039788-$ or US-20060137969-$).did. or (US-3601887-$ or US-3952939-$ or US-5207864-$ or US-5262347-$ or US-5376580-$ or US-6962834-$ or US-6443179-$ or US-4587700-$ or US-3849865-$ or US-3869779-$ or US-4110084-$ or US-4124401-$ or US-4210269-$ or US-4218007-$ or US-4605343-$ or US-5039570-$ or US-6189766-$ or US-6264095-$ or US-5215639-$ or US-6793124-$ or US-6521108-$ or US-6392208-$ or US-4331476-$ or US-3523148-$).did. or (US-3788926-$ or US-3192092-$ or US-3340053-$).did. or (WO-3025997-$).did. or (JP-03084713-$).did. or (JP-01208373-$ or US-3904101-$ or US-4218007-$ or WO-03025997-A-$ or US-20030047589-$ or US-4124401-$).did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2010/01/13 10:38

S66	0	("1andargon").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/13 10:38
S67	20	S65 and argon	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/13 10:38
S68	13	S67 and silicon	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/13 10:38

EAST Search History (Interference)

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